- 45. (Previously Presented) The semiconductor device as recited in Claim 44 wherein the MOSFET has a breakdown voltage greater than an operating voltage of the CMOS device.
- 46. (Previously Presented) The semiconductor device as recited in Claim 44 wherein the MOSFET has a breakdown voltage of at least about 10 volts and the CMOS device has a breakdown voltage between about 3 volts and 5 volts.
- 47. (Previously Presented) The semiconductor device as recited in Claim 44 wherein the semiconductor device is a power converter and the MOSFET is a power switch for the power converter.

## Claim 48 (Canceled)

- 49. (Previously Presented) The semiconductor device as recited in Claim 44 wherein the silicon carbide tub is located over the conductive substrate.
- 50. (Previously Presented) The semiconductor device as recited in Claim 44 wherein the material is doped silicon, wherein the silicon is doped with a p-type dopant or an n-type dopant.

- 51. (Previously Presented) The semiconductor device as recited in Claim 44 wherein the source and drain regions are doped with a p-type dopant or an n-type dopant.
- 52. (Previously Presented) The semiconductor device as recited in Claim 44 further comprising a buried oxide layer formed in the conductive substrate.
- 53. (Previously Presented) The semiconductor device as recited in Claim 44 wherein the conductive substrate comprises silicon and wherein the silicon carbide tub comprises a 3C silicon carbide.

Kindly cancel Claim 54 without prejudice or disclaimer.